



## STD2NB80

### N - CHANNEL 800V - 4.6 $\Omega$ - 1.9A - IPAK/DPAK PowerMESH™ MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD2NB80	800 V	< 6.5 $\Omega$	1.9 A

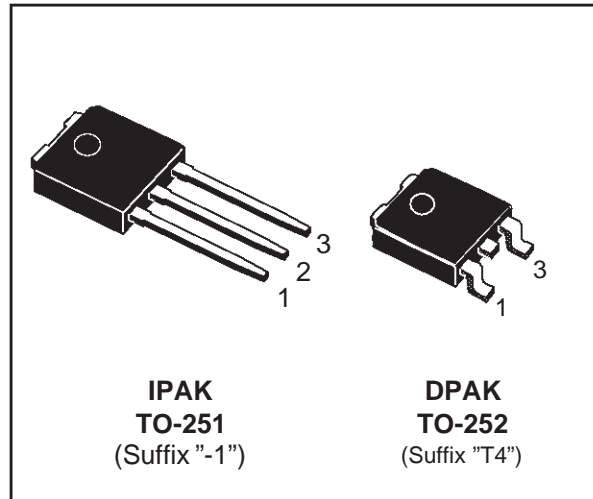
- TYPICAL R<sub>DS(on)</sub> = 4.6  $\Omega$
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL (2500 UNITS)

#### DESCRIPTION

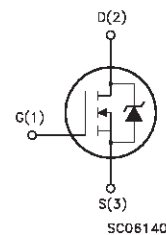
Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R<sub>DS(on)</sub> per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

#### APPLICATIONS

- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



#### INTERNAL SCHEMATIC DIAGRAM



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	800	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	800	V
V <sub>GS</sub>	Gate-source Voltage	$\pm 30$	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	1.9	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	1.2	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	7.6	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	55	W
	Derating Factor	0.44	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	4.5	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub>  $\leq$  2A, di/dt  $\leq$  200 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  V<sub>(BR)DSS</sub>, T<sub>j</sub>  $\leq$  T<sub>JMAX</sub>

## STD2NB80

### THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.27	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	100	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	1	$^{\circ}C/W$
$T_I$	Maximum Lead Temperature For Soldering Purpose		275	$^{\circ}C$

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max)	1.9	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$ , $I_D = I_{AR}$ , $V_{DD} = 50 V$ )	176	mJ

### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	800			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 50	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 30 V$			$\pm 100$	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 1.3 A$		4.6	6.5	$\Omega$
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	1.9			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.3 A$	1	2		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		440 60 7		pF pF pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay Time	$V_{DD} = 400\text{ V}$ $I_D = 1.5\text{ A}$		12		ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		10		ns
$Q_g$	Total Gate Charge	$V_{DD} = 640\text{ V}$ $I_D = 3\text{ A}$ $V_{GS} = 10\text{ V}$		17	24	nC
$Q_{gs}$	Gate-Source Charge			6.5		nC
$Q_{gd}$	Gate-Drain Charge			7.5		nC

**SWITCHING OFF**

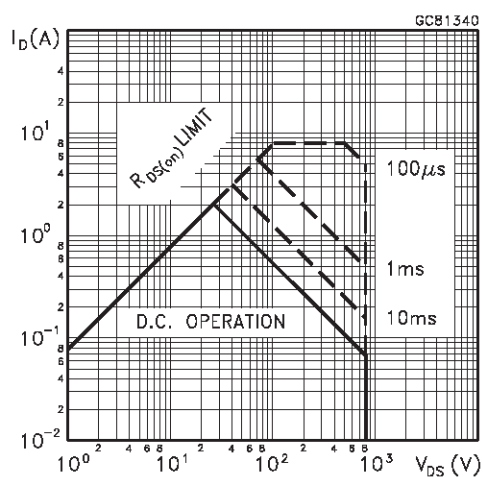
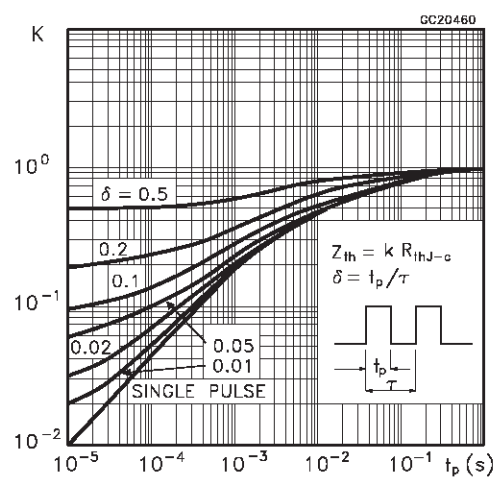
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 3\text{ A}$		15		ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		17		ns
$t_c$	Cross-over Time			22		ns

**SOURCE DRAIN DIODE**

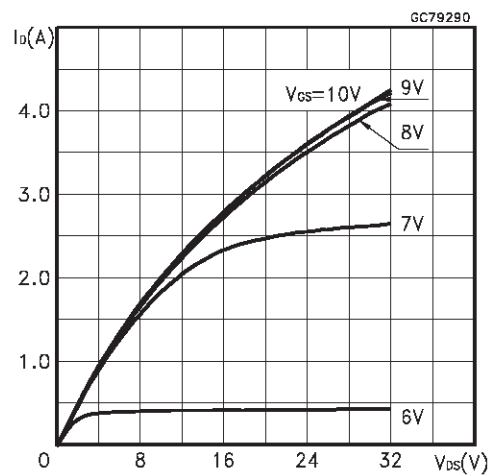
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				1.9	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				7.6	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 1.9\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 2.6\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		650		ns
$Q_{rr}$	Reverse Recovery Charge			2.8		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			8.5		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

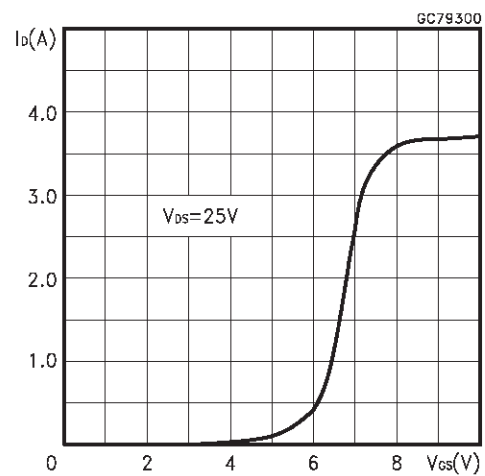
(•) Pulse width limited by safe operating area

**Safe Operating Area****Thermal Impedance**

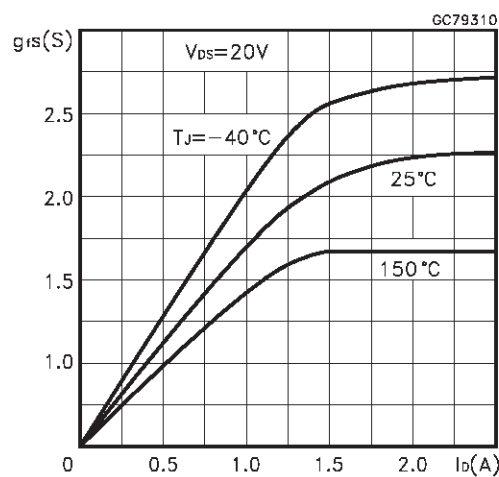
Output Characteristics



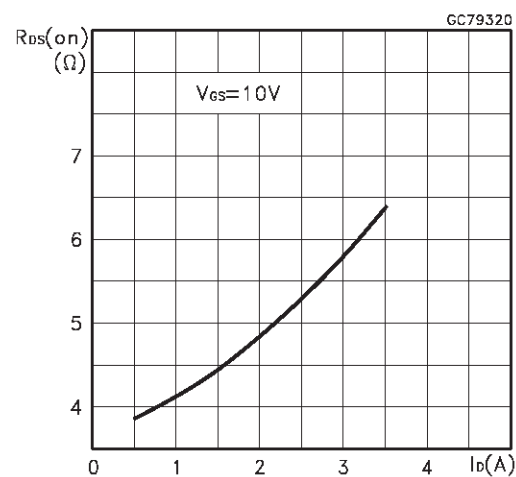
Transfer Characteristics



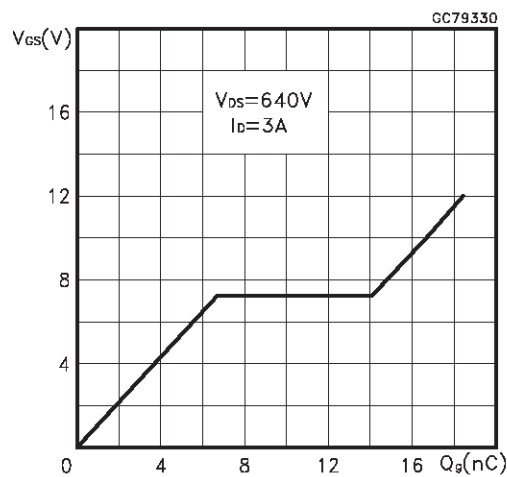
Transconductance



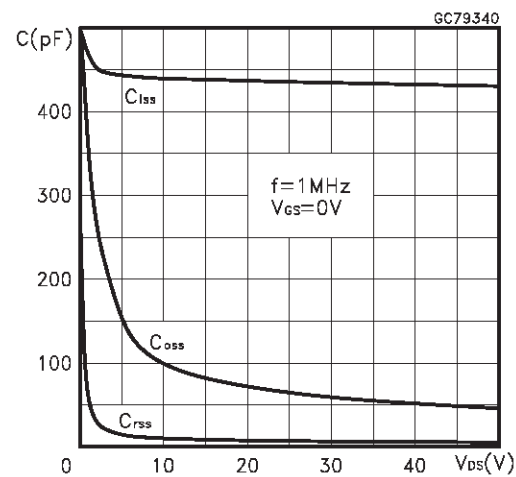
Static Drain-source On Resistance



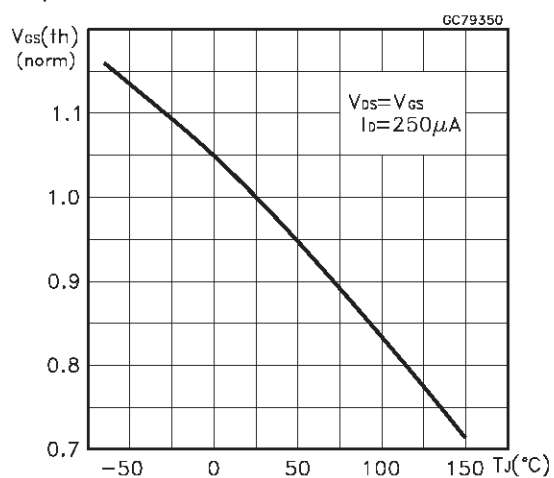
Gate Charge vs Gate-source Voltage



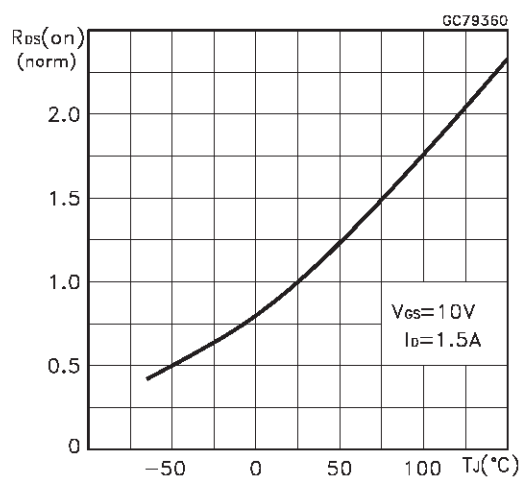
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

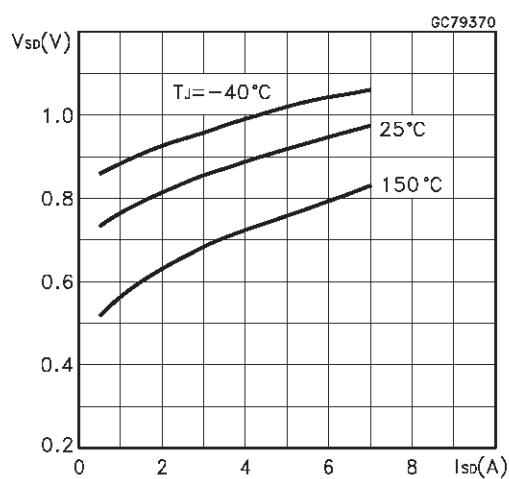


Fig. 1: Unclamped Inductive Load Test Circuit

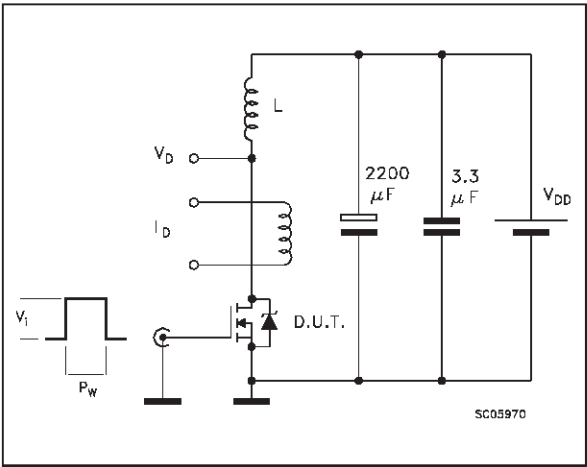


Fig. 2: Unclamped Inductive Waveform

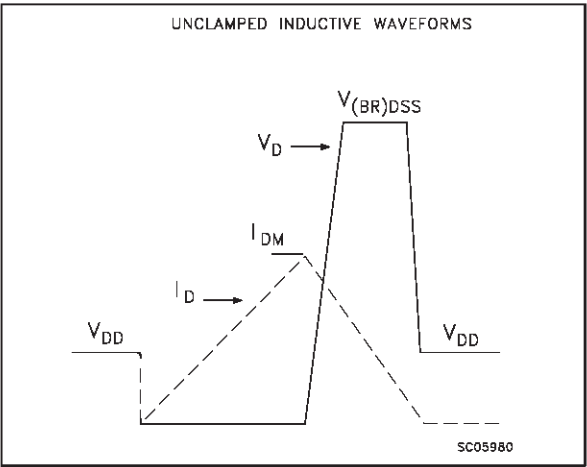


Fig. 3: Switching Times Test Circuits For Resistive Load

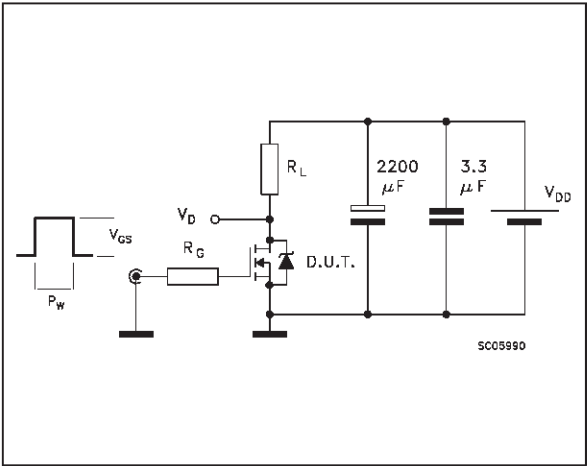


Fig. 4: Gate Charge test Circuit

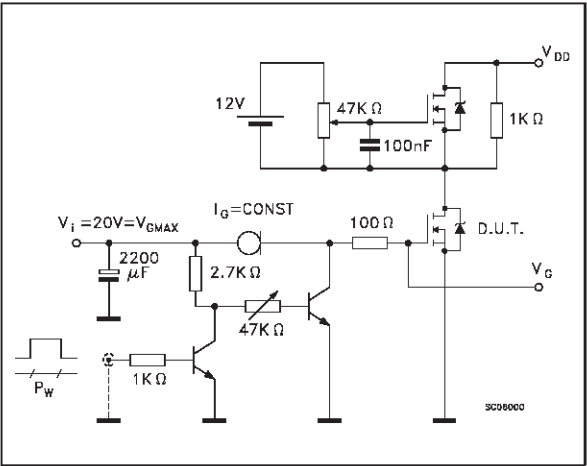
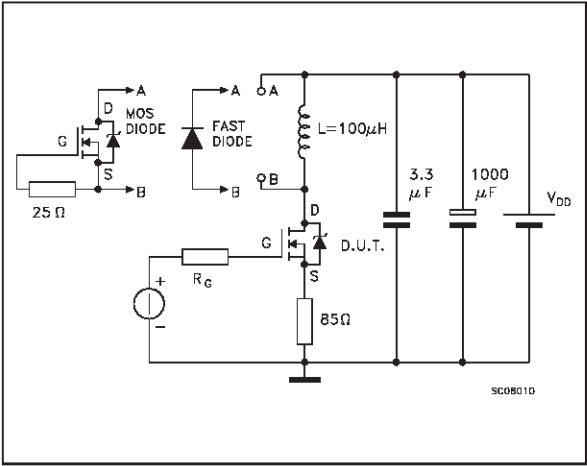
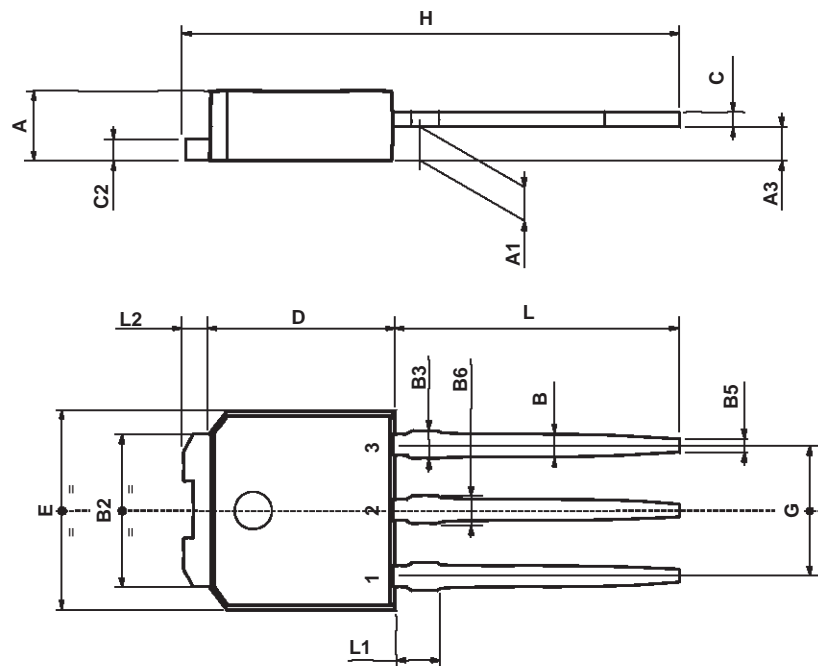


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



## TO-251 (IPAK) MECHANICAL DATA

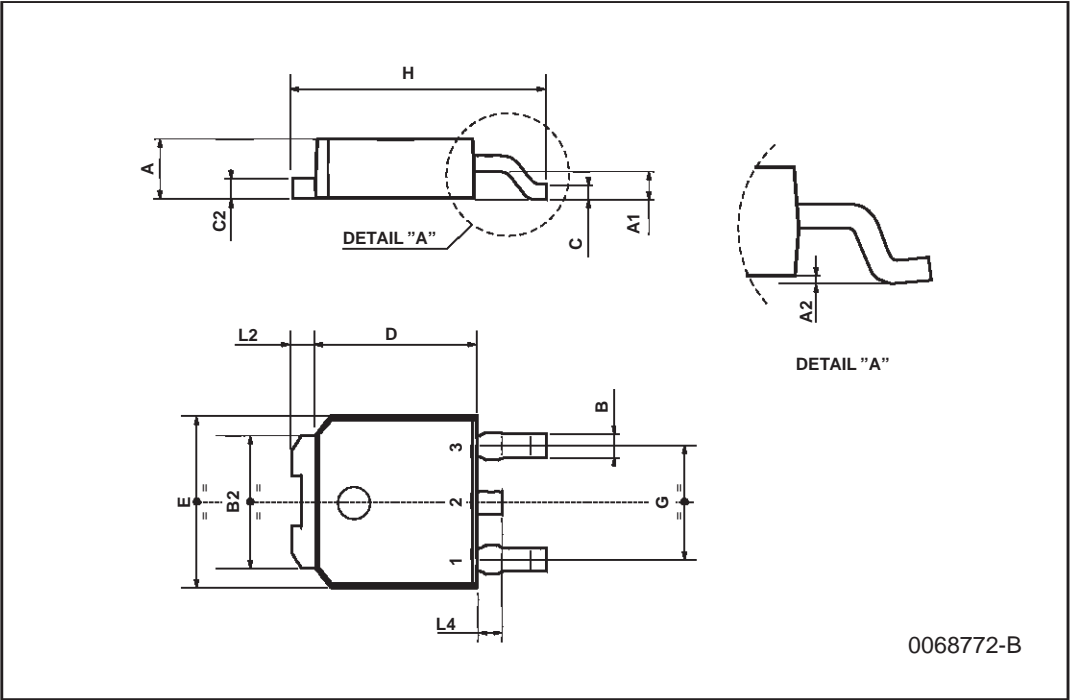
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



0068771-E

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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